



Features

- ◇ Glass passivated junction chip
- ◇ For surface mounted applications
- ◇ Low profile package
- ◇ Built-in strain relief
- ◇ Ideal for automated placement
- ◇ Easy pick and place
- ◇ Super fast recovery time for high efficiency
- ◇ Glass passivated chip junction
- ◇ High temperature soldering:
260°C/10 seconds at terminals
- ◇ Plastic material used carries Underwriters
Laboratory Classification 94V-0

Mechanical Data

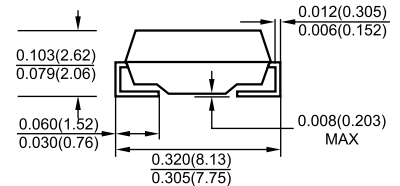
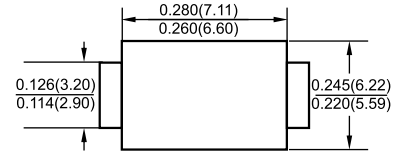
- ◇ Cases: Molded plastic
- ◇ Terminals: Pure tin plated, lead free.
- ◇ Polarity: Indicated by cathode band
- ◇ Weight: 0.21 gram

Marking Information



LGE: Lu Guang Electronic
XXXX: marking code (ES3A-ES3J)

SMC/DO-214AB



Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

| Type Number | Symbol | ES 3A | ES 3B | ES 3C | ES 3D | ES 3F | ES 3G | ES 3H | ES 3J | Units |
|--|------------------------------------|-------------|-------|-------|-------|-------|-------|-------|-------|--------------------|
| Maximum Recurrent Peak Reverse Voltage | V_{RRM} | 50 | 100 | 150 | 200 | 300 | 400 | 500 | 600 | V |
| Maximum RMS Voltage | V_{RMS} | 35 | 70 | 105 | 140 | 210 | 280 | 350 | 420 | V |
| Maximum DC Blocking Voltage | V_{DC} | 50 | 100 | 150 | 200 | 300 | 400 | 500 | 600 | V |
| Maximum Average Forward Rectified Current See Fig. 1 | $I_{(AV)}$ | 3.0 | | | | | | | | A |
| Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method) @ $T_L = 100^\circ\text{C}$ | I_{FSM} | 100 | | | | | | | | A |
| Maximum Instantaneous Forward Voltage @ 3.0A | V_F | 0.95 | | | 1.3 | | 1.7 | | | V |
| Maximum DC Reverse Current @ $T_A = 25^\circ\text{C}$ at Rated DC Blocking Voltage @ $T_A = 100^\circ\text{C}$ | I_R | 10 | | | | 500 | | | | μA |
| Maximum Reverse Recovery Time (Note 1) | T_{rr} | 35 | | | | | | | | nS |
| Typical Junction Capacitance (Note 2) | C_j | 45 | | | | 30 | | | | pF |
| Typical Thermal Resistance (Note 3) | $R_{\theta JA}$ $R_{\theta JL}$ | 47 | | | | 12 | | | | $^\circ\text{C/W}$ |
| Operating Temperature Range | T_J | -55 to +150 | | | | | | | | $^\circ\text{C}$ |
| Storage Temperature Range | T_{STG} | -55 to +150 | | | | | | | | $^\circ\text{C}$ |

- Notes:
1. Reverse Recovery Test Conditions: $I_F=0.5A$, $I_R=1.0A$, $I_{RR}=0.25A$
 2. Measured at 1 MHz and Applied $V_R=4.0$ Volts
 3. Units Mounted on P.C.B. with 0.6" x 0.6"(16mm x 16mm) Copper Pad Areas

RATINGS AND CHARACTERISTIC CURVES (ES3A THRU ES3J)

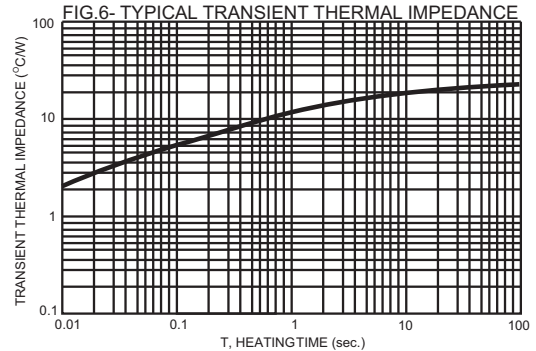
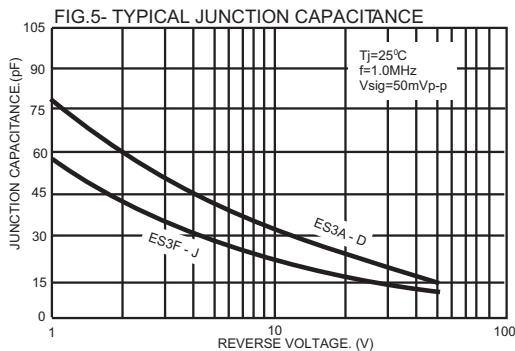
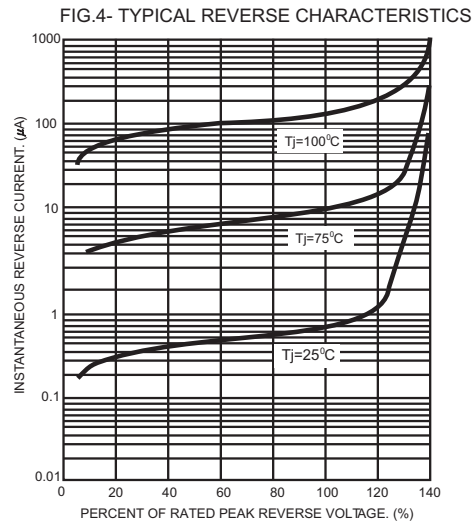
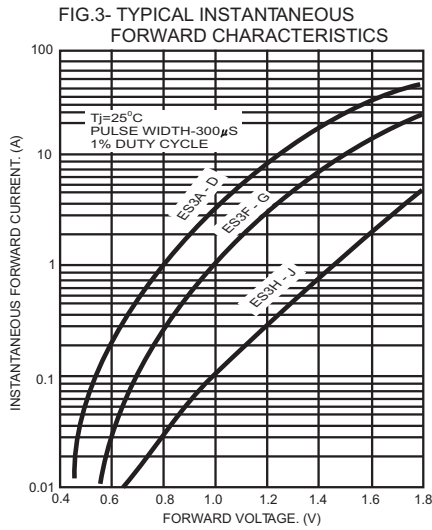
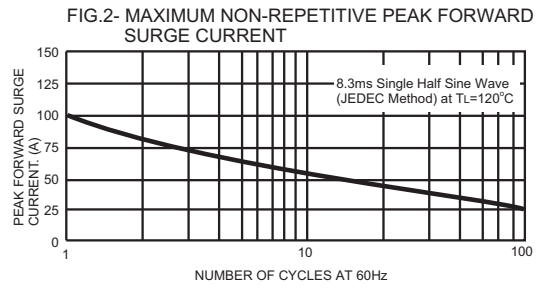
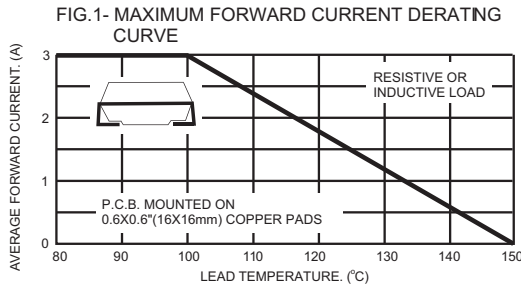


FIG.7- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM

